



Complementary N- and P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY			
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (mA)
N-Channel	60	1.40 at V _{GS} = 10 V	500
		3 at V _{GS} = 4.5 V	200
P-Channel	- 60	4 at V _{GS} = - 10 V	- 500
		8 at V _{GS} = - 4.5 V	- 25

FEATURES

- Halogen-free Option Available
- TrenchFET[®] Power MOSFETs
- Very Small Footprint
- High-Side Switching
- Low On-Resistance:
N-Channel, 1.40 Ω
P-Channel, 4 Ω
- Low Threshold: ± 2 V (typ.)
- Fast Switching Speed: 15 ns (typ.)
- Gate-Source ESD Protected: 2000 V



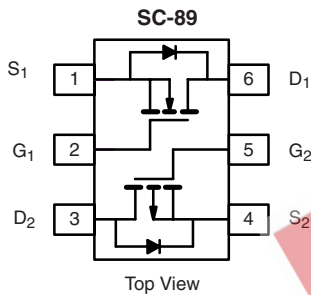
RoHS COMPLIANT

BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits

APPLICATIONS

- Replace Digital Transistor, Level-Shifter
- Battery Operated Systems
- Power Supply Converter Circuits



Marking Code: H

Ordering Information: Si1029X-T1-E3 (Lead (Pb)-free)
Si1029X-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted							
Parameter	Symbol	N-Channel		P-Channel		Unit	
		5 s	Steady State	5 s	Steady State		
Drain-Source Voltage	V _{DS}	60		- 60		V	
Gate-Source Voltage	V _{GS}	± 20					
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	320	305	- 200	- 190	mA
		T _A = 85 °C	230	220	- 145	- 135	
Pulsed Drain Current ^b	I _{DM}	650		- 650			
Continuous Source Current (Diode Conduction) ^a	I _S	450	380	- 450	- 380		
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	280	250	280	250	mW
		T _A = 85 °C	145	130	145	130	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150				°C	
Gate-Source ESD Rating (HBM, Method 3015)	ESD	2000				V	

Notes:

a. Surface Mounted on FR4 board.

b. Pulse width limited by maximum junction temperature.

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SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 10\text{ }\mu\text{A}$	N-Ch	60		V
		$V_{GS} = 0\text{ V}, I_D = -10\text{ }\mu\text{A}$	P-Ch	-60		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	N-Ch	1	2.5	V
		$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-1	-3.0	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{ V}$	N-Ch		± 50	nA
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}$	N-Ch		± 100	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}$	N-Ch		10	
		$V_{DS} = -50\text{ V}, V_{GS} = 0\text{ V}$	P-Ch		-25	
		$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$	N-Ch		100	
		$V_{DS} = -50\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$	P-Ch		-250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}$	N-Ch	500		mA
		$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}$	P-Ch	-50		
		$V_{DS} = 7.5\text{ V}, V_{GS} = -4.5\text{ V}$	N-Ch	800		
		$V_{DS} = -10\text{ V}, V_{GS} = -10\text{ V}$	P-Ch	-600		
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 200\text{ mA}$	N-Ch		3	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -25\text{ mA}$	P-Ch		8	
		$V_{GS} = 10\text{ V}, I_D = 500\text{ mA}$	N-Ch		1.40	
		$V_{GS} = -10\text{ V}, I_D = -500\text{ mA}$	P-Ch		4	
		$V_{GS} = 10\text{ V}, I_D = 500\text{ mA}, T_J = 125\text{ }^\circ\text{C}$	N-Ch		2.50	
		$V_{GS} = -10\text{ V}, I_D = -500\text{ mA}, T_J = 125\text{ }^\circ\text{C}$	P-Ch		6	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 200\text{ mA}$	N-Ch		200	ms
		$V_{DS} = -10\text{ V}, I_D = -100\text{ mA}$	P-Ch		100	
Diode Forward Voltage ^a	V_{SD}	$I_S = 200\text{ mA}, V_{GS} = 0\text{ V}$	N-Ch		1.4	V
		$I_S = -200\text{ mA}, V_{GS} = 0\text{ V}$	P-Ch		-1.4	
Dynamic^b						
Total Gate Charge	Q_g	N-Channel $V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 250\text{ mA}$	N-Ch		750	pC
Gate-Source Charge	Q_{gs}		P-Ch		1700	
Gate-Drain Charge	Q_{gd}	P-Channel $V_{DS} = -30\text{ V}, V_{GS} = -15\text{ V}, I_D = -500\text{ mA}$	N-Ch		75	
			P-Ch		260	
Input Capacitance	C_{iss}	N-Channel $V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	N-Ch		30	pF
Output Capacitance	C_{oss}		P-Ch		23	
Reverse Transfer Capacitance	C_{rss}	P-Channel $V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	N-Ch		6	
			P-Ch		10	
Turn-On Time ^c	t_{ON}	N-Channel $V_{DD} = 30\text{ V}, R_L = 150\text{ }\Omega$ $I_D \cong 200\text{ mA}, V_{GEN} = 10\text{ V}, R_G = 10\text{ }\Omega$	N-Ch		15	
			P-Ch		20	
Turn-Off Time ^c	t_{OFF}	P-Channel $V_{DD} = -25\text{ V}, R_L = 150\text{ }\Omega$ $I_D \cong -165\text{ mA}, V_{GEN} = -10\text{ V}, R_G = 10\text{ }\Omega$	N-Ch		20	
			P-Ch		35	

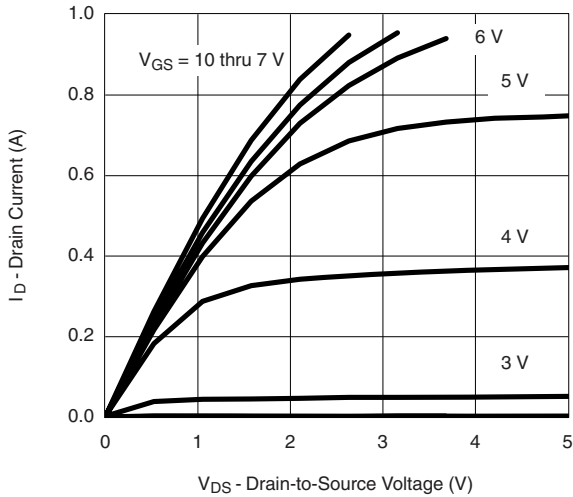
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.

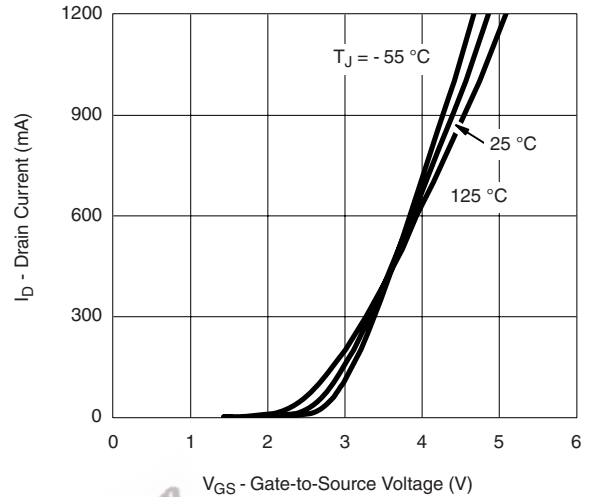
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



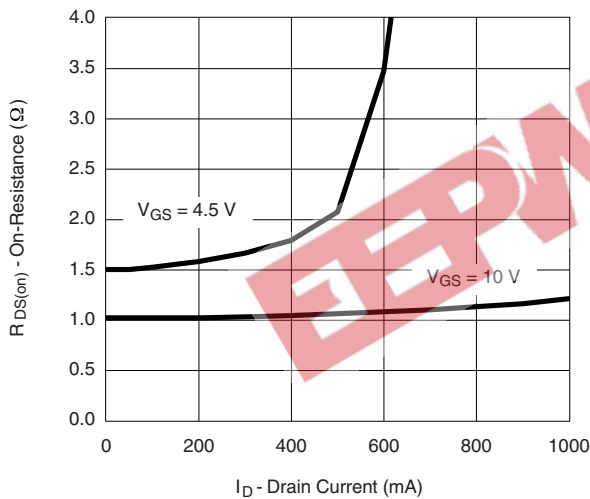
N-CHANNEL TYPICAL CHARACTERISTICS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted



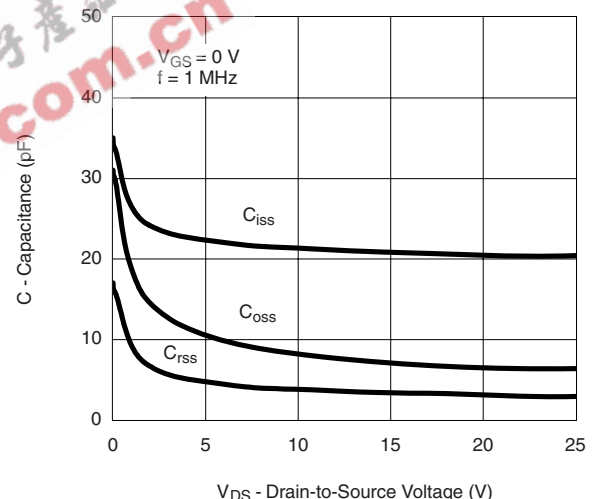
Output Characteristics



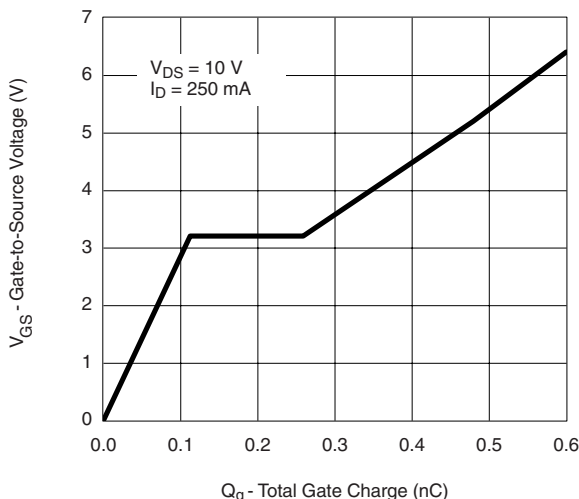
Transfer Characteristics



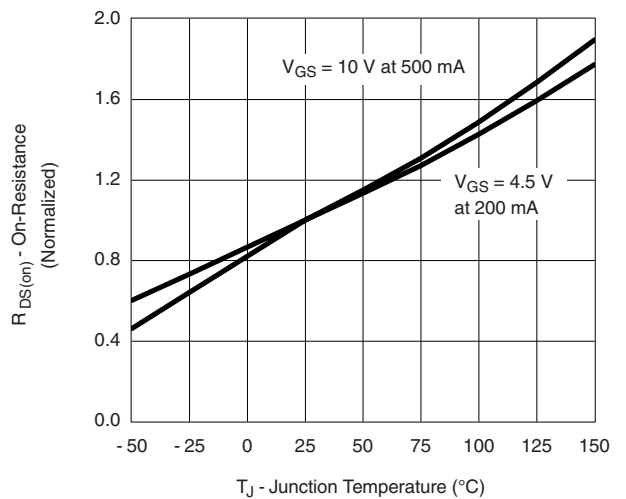
On-Resistance vs. Drain Current



Capacitance



Gate Charge



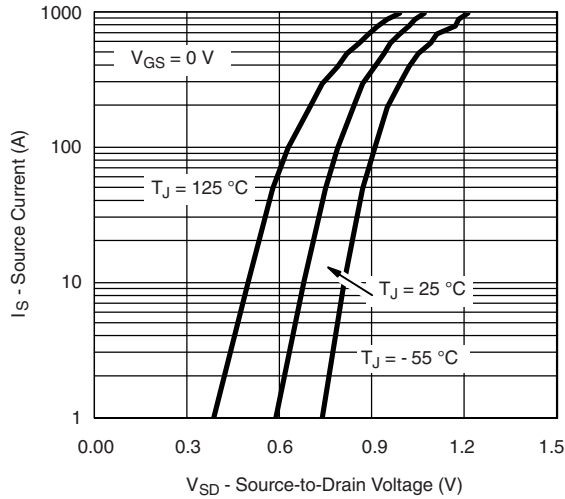
On-Resistance vs. Junction Temperature

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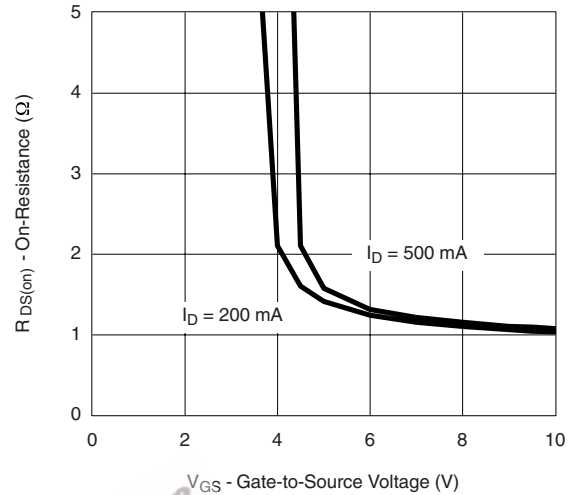
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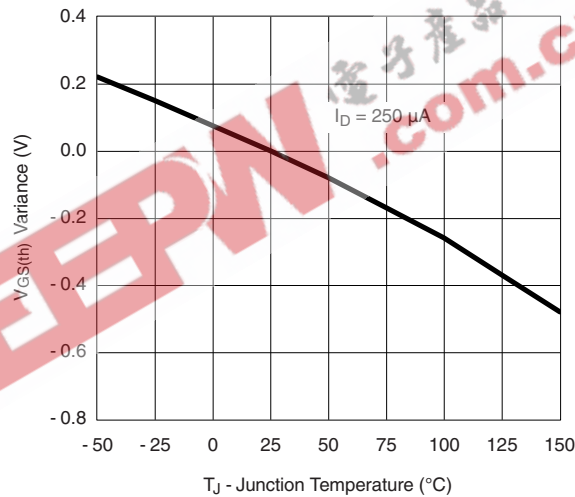
N-CHANNEL TYPICAL CHARACTERISTICS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted



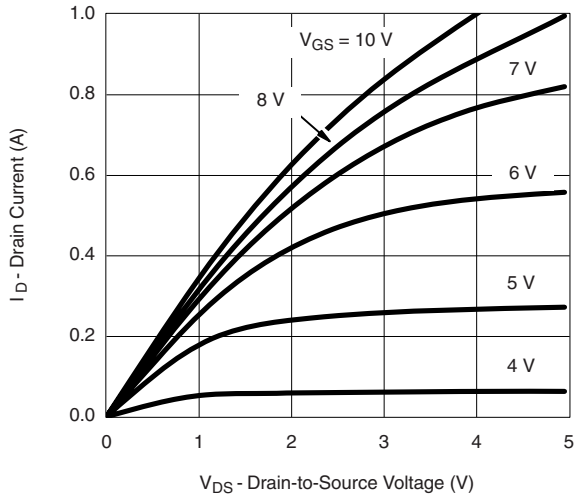
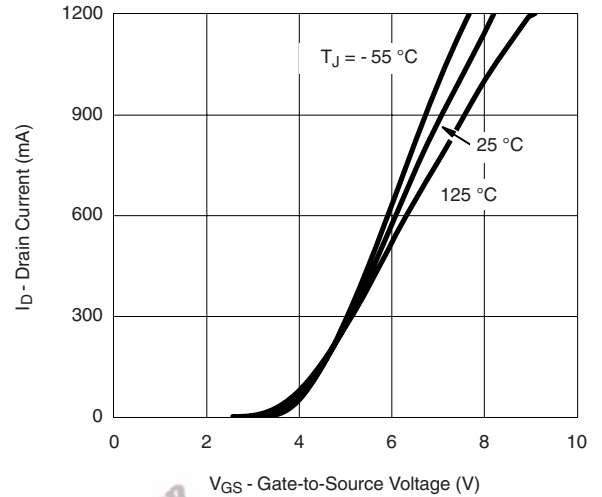
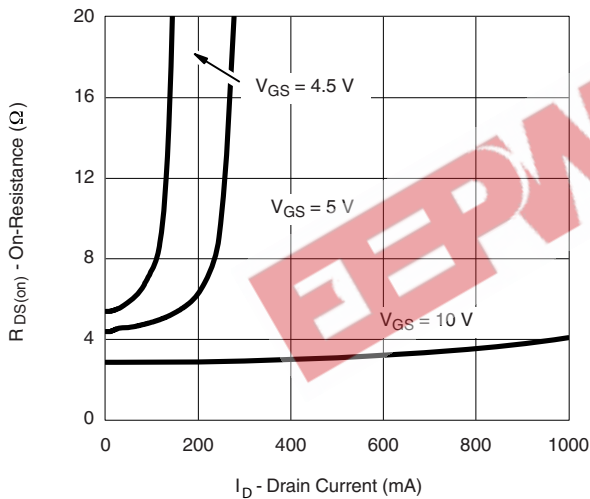
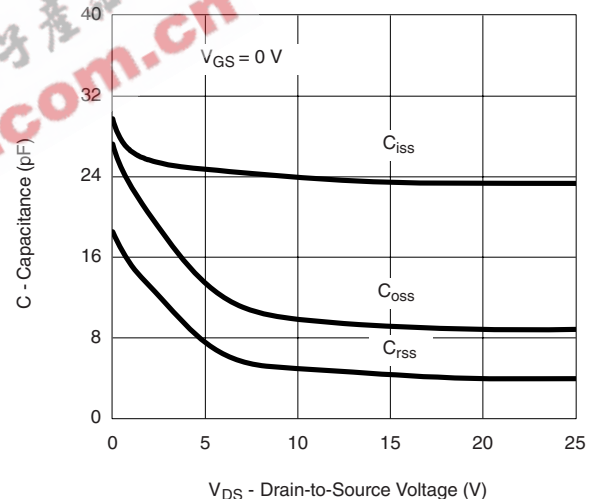
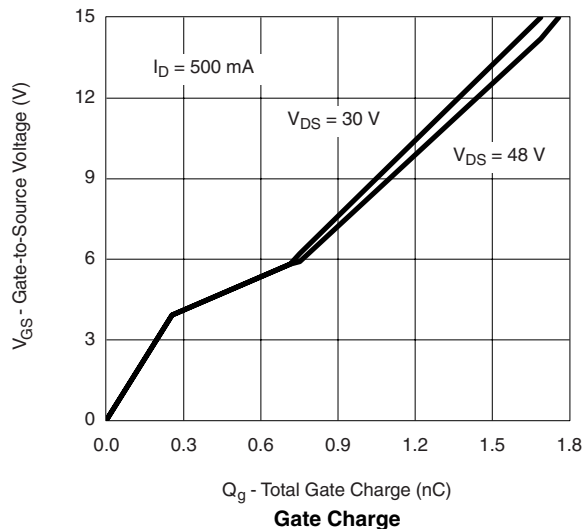
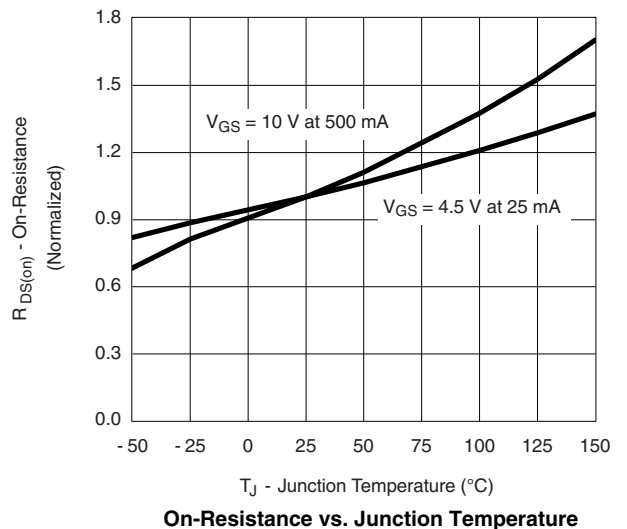
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage Variance Over Temperature

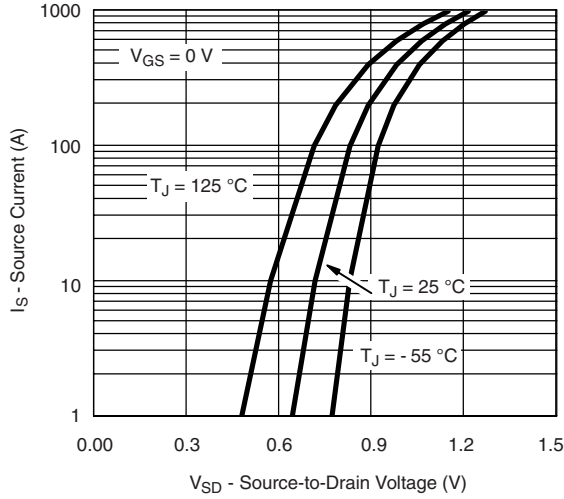
P-CHANNEL TYPICAL CHARACTERISTICS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

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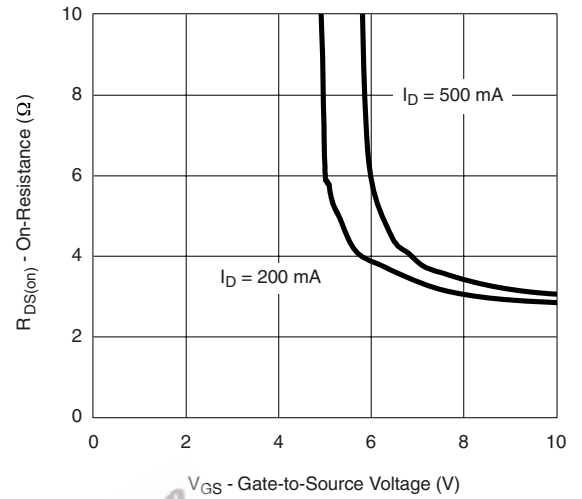
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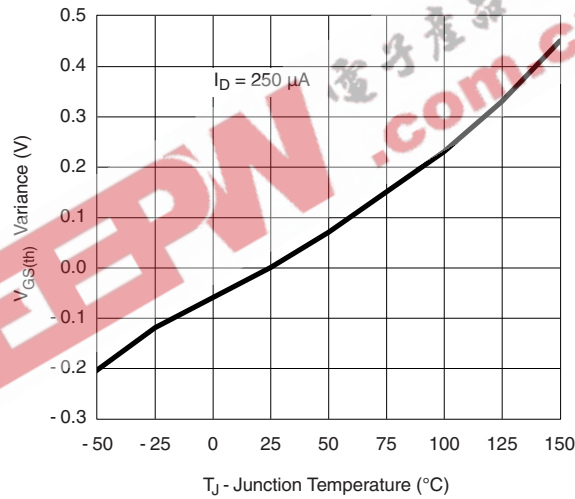
P-CHANNEL TYPICAL CHARACTERISTICS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted



Source-Drain Diode Forward Voltage



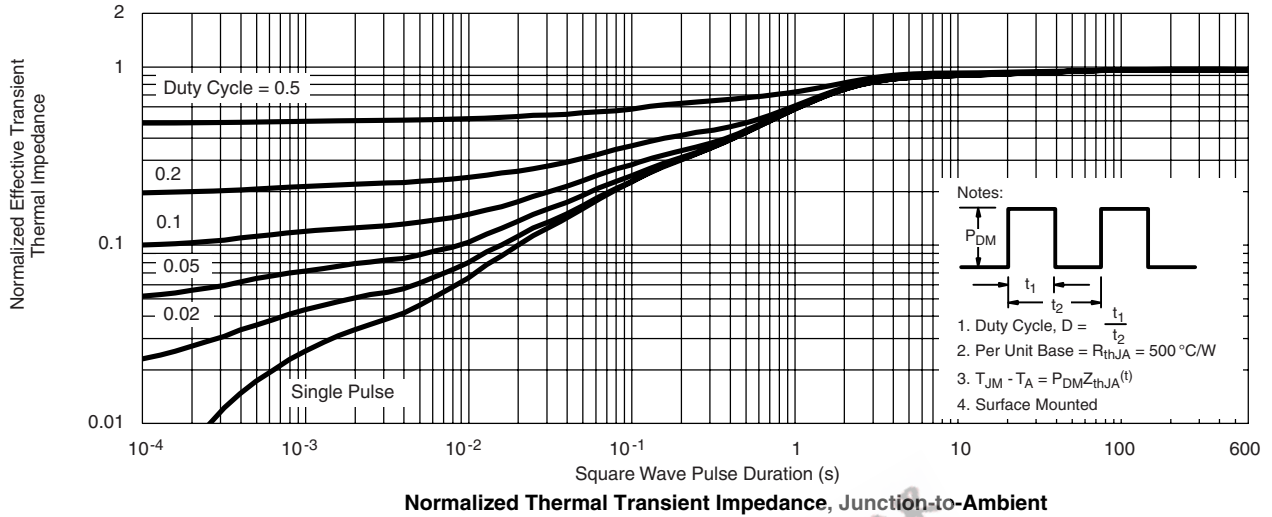
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage Variance Over Temperature



N- OR P-CHANNEL TYPICAL CHARACTERISTICS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted



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